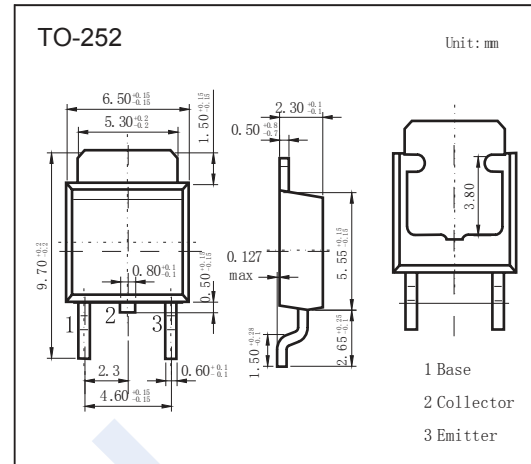


PNP Transistors

2SB1201

■ Features

- Low collector-to-emitter saturation voltage.
- Fast switching speed.
- Large current capacity and wide ASO.
- Complementary to 2SD1801

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-60	V
Collector - Emitter Voltage	V_{CEO}	-50	
Emitter - Base Voltage	V_{EBO}	-6	
Collector Current - Continuous	I_C	-2	A
Collector Current - Pulse	I_{CP}	-4	
Collector Power Dissipation $T_c = 25^\circ\text{C}$	P_C	15	W
		0.8	
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

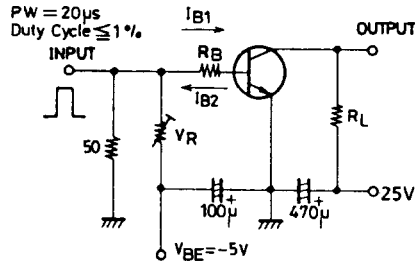
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -100 \mu\text{A}$, $I_E = 0$	-60			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1 \text{ mA}$, $R_{BE} = \infty$	-50			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100 \mu\text{A}$, $I_C = 0$	-6			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -50\text{V}$, $I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}$, $I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1 \text{ A}$, $I_B = -50\text{mA}$		-0.3	-0.7	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1 \text{ A}$, $I_B = -50\text{mA}$		-0.9	-1.2	
DC current gain	h_{FE}	$V_{CE} = -2\text{V}$, $I_C = -100 \text{ mA}$	100		560	
		$V_{CE} = -2\text{V}$, $I_C = -1.5 \text{ A}$	40			
Turn-ON Time	t_{on}	See specified Test Circuit		60		ns
Storage Time	t_{stg}			450		
Fall Time	t_f			30		
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$		22		pF
Transition frequency	f_T	$V_{CE} = -10\text{V}$, $I_C = -50\text{mA}$		150		MHz

■ Classification of $h_{FE}(1)$

Type	2SB1201-R	2SB1201-S	2SB1201-T	2SB1201-U
Range	100-200	140-280	200-400	280-560

PNP Transistors 2SB1201

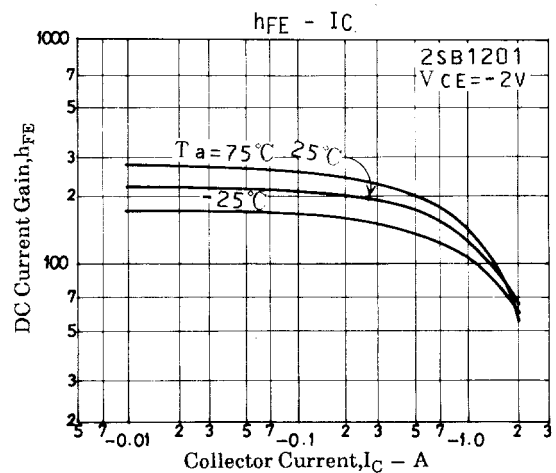
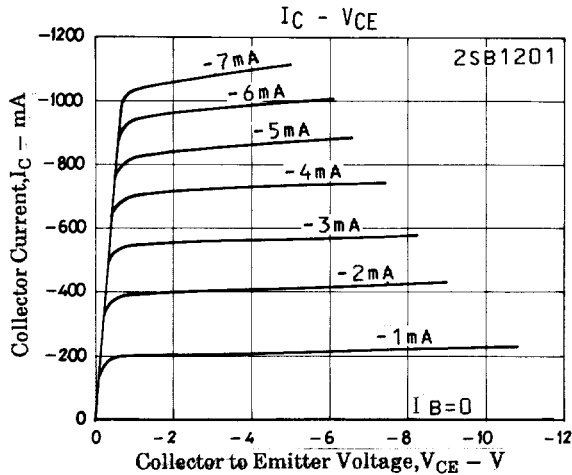
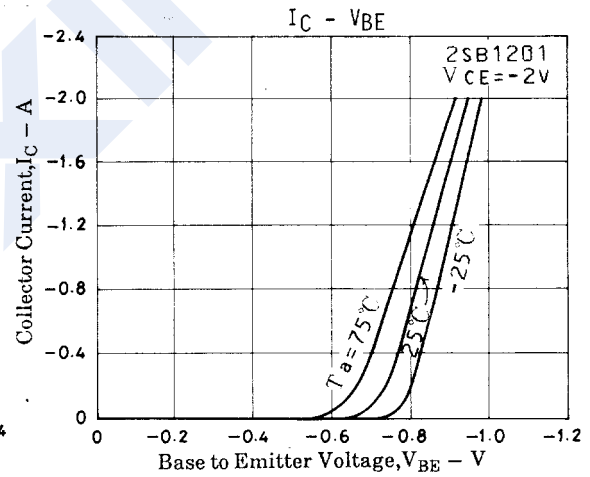
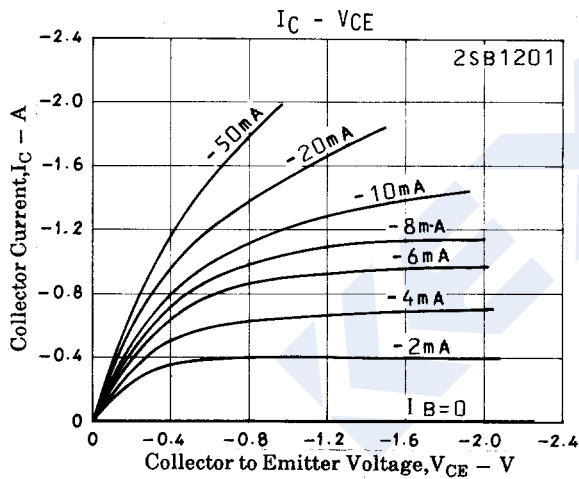
Switching Time Test Circuit



$I_C = 10 I_{B1} = -10 I_{B2} = 500\text{mA}$, $V_{CE} = 25\text{V}$
(For PNP, the polarity is reversed.)

Unit (resistance : Ω , capacitance : F)

■ Typical Characteristics



PNP Transistors

2SB1201

■ Typical Characteristics

